



# STD90N03L STD90N03L-1

N-channel 30V - 0.005Ω - 80A - DPAK/IPAK  
STripFET™ III Power MOSFET

## General features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STD90N03L	30V	0.0057Ω	80A <sup>(1)</sup>
STD90N03L-1	30V	0.0057Ω	80A <sup>(1)</sup>

1. Pulse width limited by safe operating area

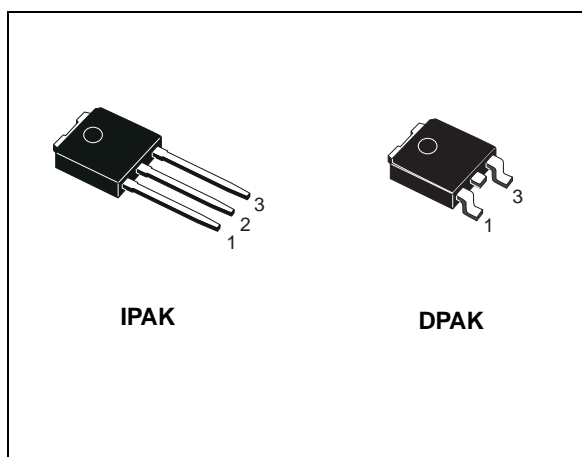
- R<sub>DS(on)</sub>\*Q<sub>g</sub> industry's benchmark
- Conduction losses reduced
- Switching losses reduced
- Low threshold device

## Description

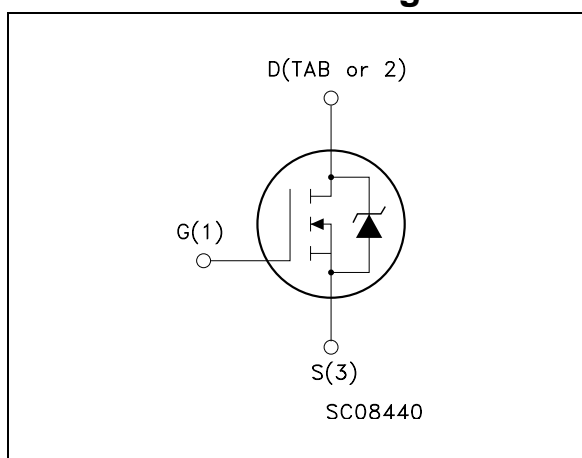
This device utilizes the latest advanced design rules of ST's proprietary STripFET™ technology. This is suitable for the most demanding DC-DC converter application where high efficiency is to be achieved.

## Applications

- Switching applications



## Internal schematic diagram



## Order codes

Part number	Marking	Package	Packaging
STD90N03L	D90N03L	DPAK	Tape & reel
STD90N03L-1	D90N03L-1	IPAK	Tube

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## Content

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# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	30	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	80	A
$I_D$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	64	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
$P_{TOT}$	Total dissipation at $T_C = 25^\circ\text{C}$	95	W
	Derating factor	0.63	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	350	mJ
$T_J$ $T_{stg}$	Operating junction temperature Storage temperature	-55 to 175	$^\circ\text{C}$

1. Value limited by wire bonding
2. Pulse width limited by safe operating area
3. Starting  $T_J = 25^\circ\text{C}$ ,  $I_D = 40\text{A}$ ,  $V_{DD} = 15\text{V}$

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.58	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	100	$^\circ\text{C}/\text{W}$
$T_J$	Maximum lead temperature for soldering purpose	275	$^\circ\text{C}$

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}C$  unless otherwise specified)

**Table 3. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu A, V_{GS} = 0$	30			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 30V$ $V_{DS} = 30V, T_C=125^{\circ}C$			1 10	$\mu A$ $\mu A$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20V$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1			V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 40A$ $V_{GS} = 5V, I_D = 40A$		0.005 0.007	0.0057 0.0011	$\Omega$ $\Omega$

**Table 4. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25V, f = 1MHz,$ $V_{GS} = 0$		2805 549 76		pF pF pF
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 15V, I_D = 80A$ $V_{GS} = 5V$ <i>(see Figure 13)</i>		22 10 7	32	nC nC nC
$R_G$	Gate input resistance	$f = 1MHz$ Gate Bias Bias=0 Test Signal Level=20mV open drain		1.2		$\Omega$

**Table 5. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on delay time Rise time	$V_{DD} = 15V, I_D = 40A,$ $R_G = 4.7\Omega, V_{GS} = 5V$ <i>(see Figure 12)</i>		19 135		ns ns
$t_{d(off)}$ $t_f$	Turn-off delay time Fall time	$V_{DD} = 15V, I_D = 40A,$ $R_G = 4.7\Omega, V_{GS} = 5V$ <i>(see Figure 12)</i>		24 33		ns ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current				80	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				320	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=40A, V_{GS}=0$			1.3	V
$t_{rr}$	Reverse recovery time	$I_{SD}=80A, di/dt = 100A/\mu s,$ $V_{DD}=19 V, T_j= 150^\circ C$ <i>(see Figure 15)</i>		36		ns
$Q_{rr}$	Reverse recovery charge			32		$\mu C$
$I_{RRM}$	Reverse recovery current			1.8		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 $\mu s$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

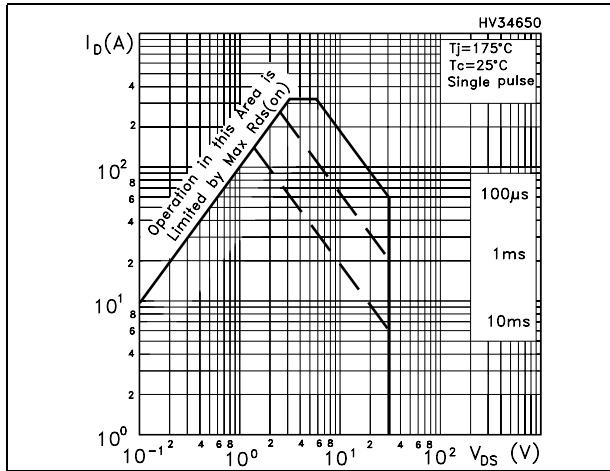


Figure 2. Thermal impedance

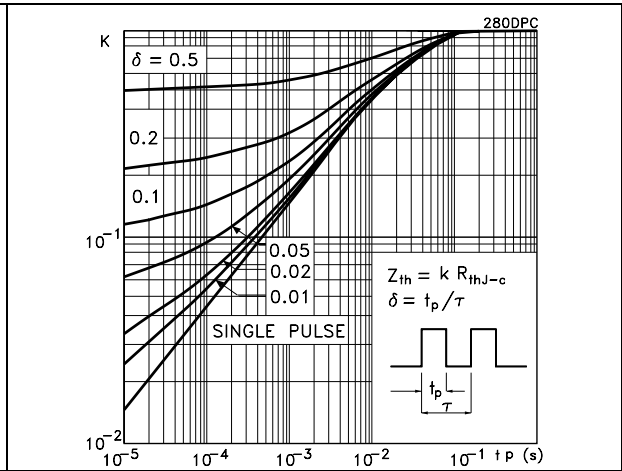


Figure 3. Output characteristics

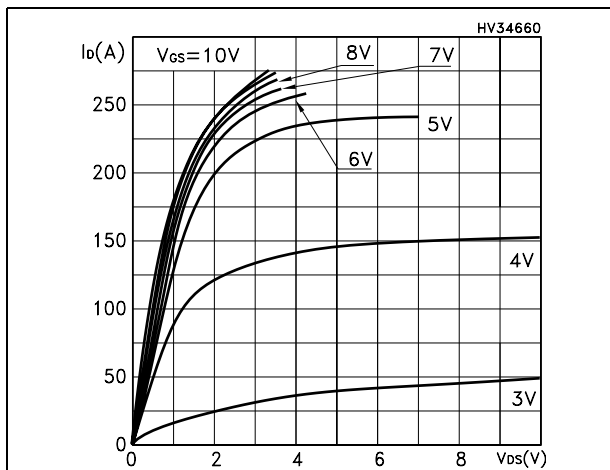


Figure 4. Transfer characteristics

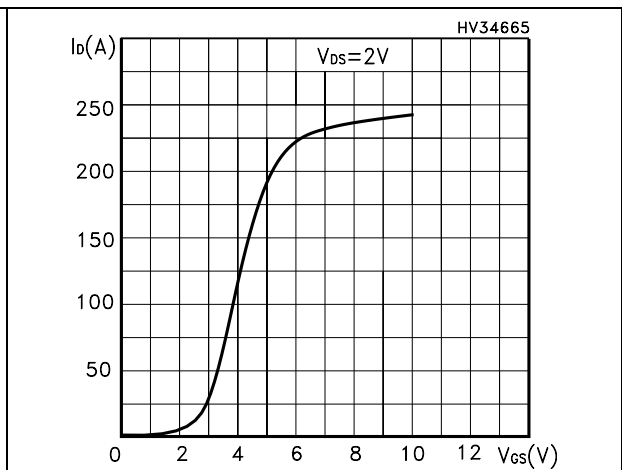


Figure 5. Static drain-source on resistance

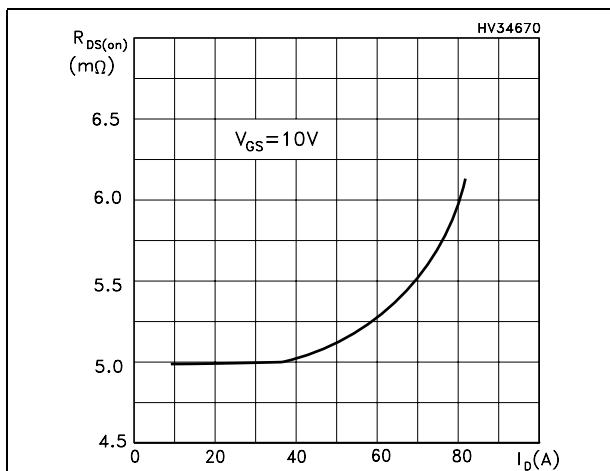


Figure 6. Normalized B\_VDSS vs temperature

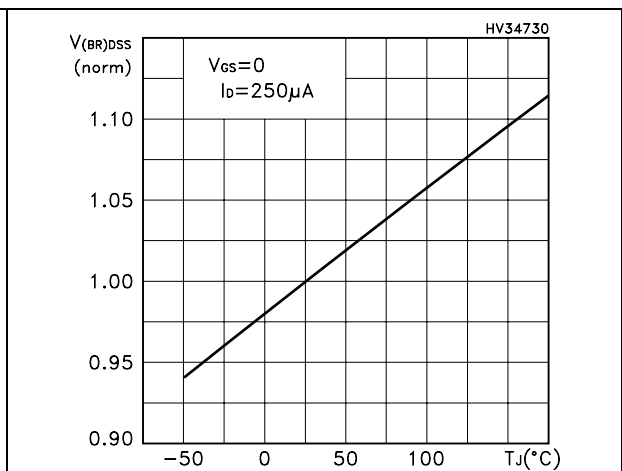


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

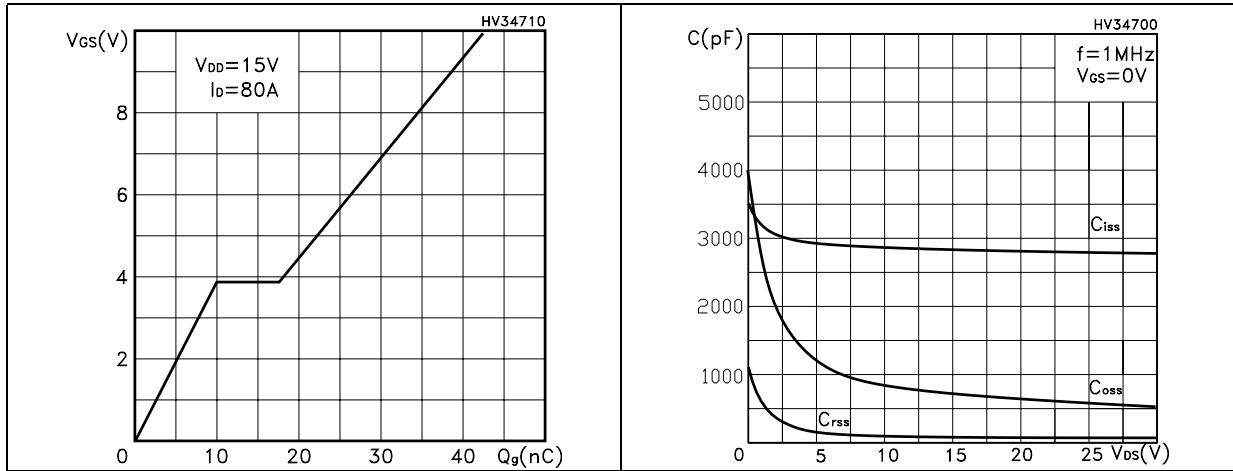


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

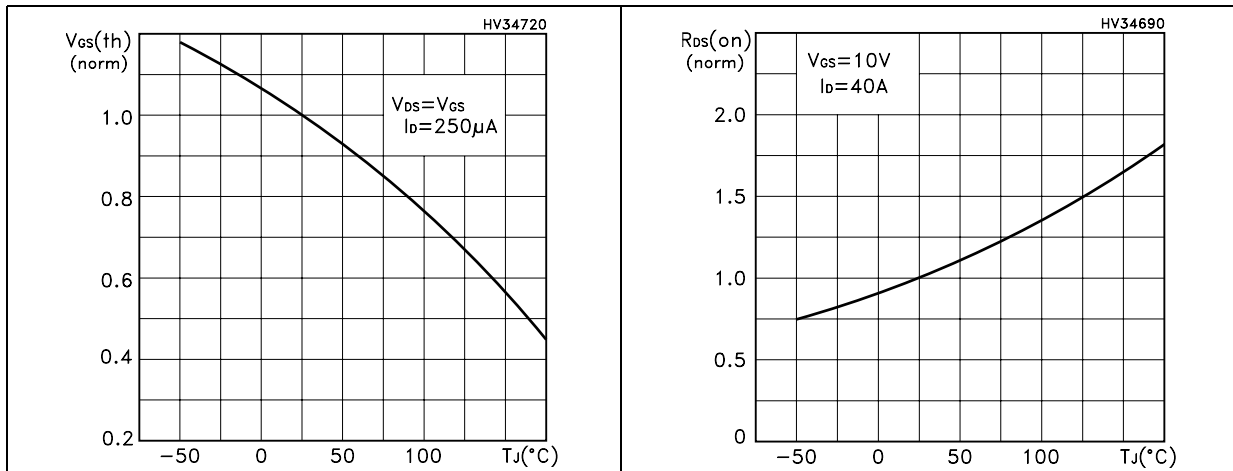
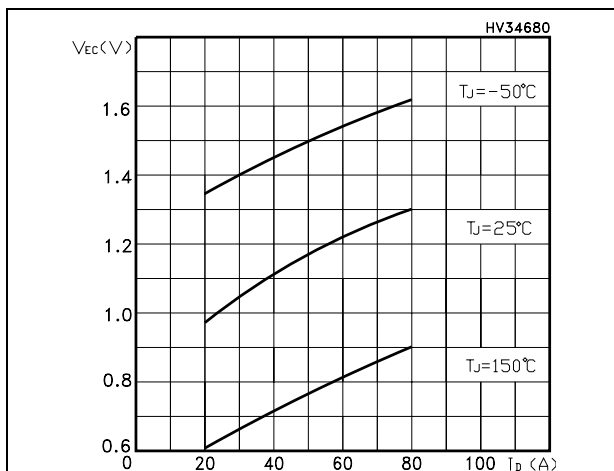


Figure 11. Source-drain diode forward characteristics



### 3 Test circuit

Figure 12. Switching times test circuit for resistive load

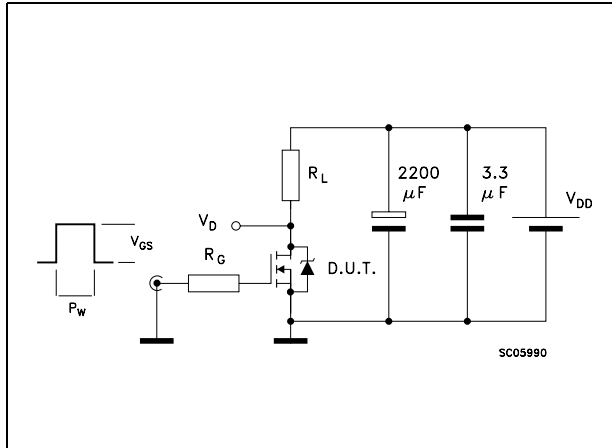


Figure 13. Gate charge test circuit

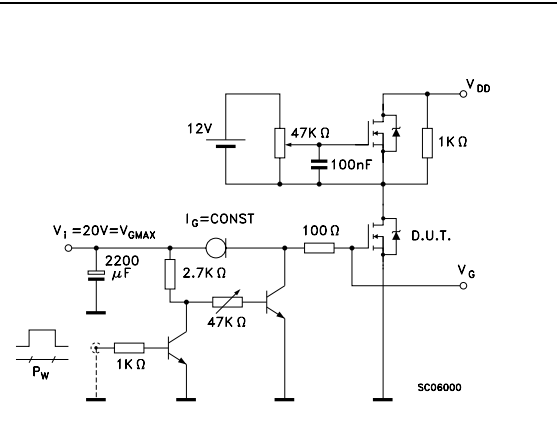


Figure 14. Test circuit for inductive load switching and diode recovery times

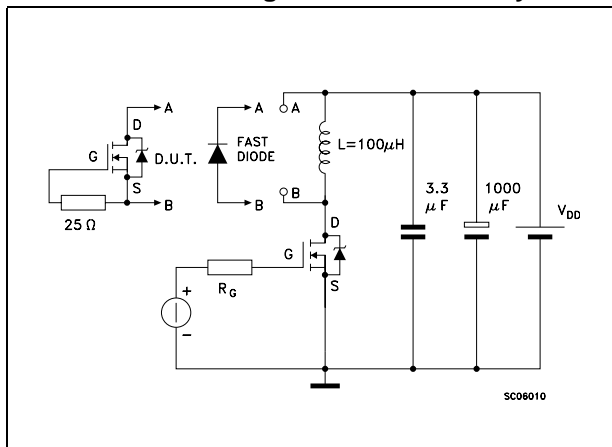
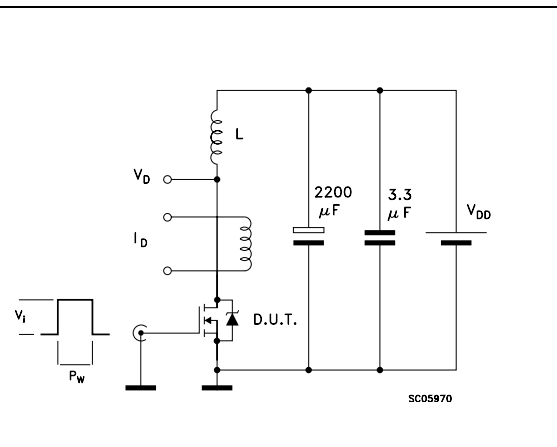


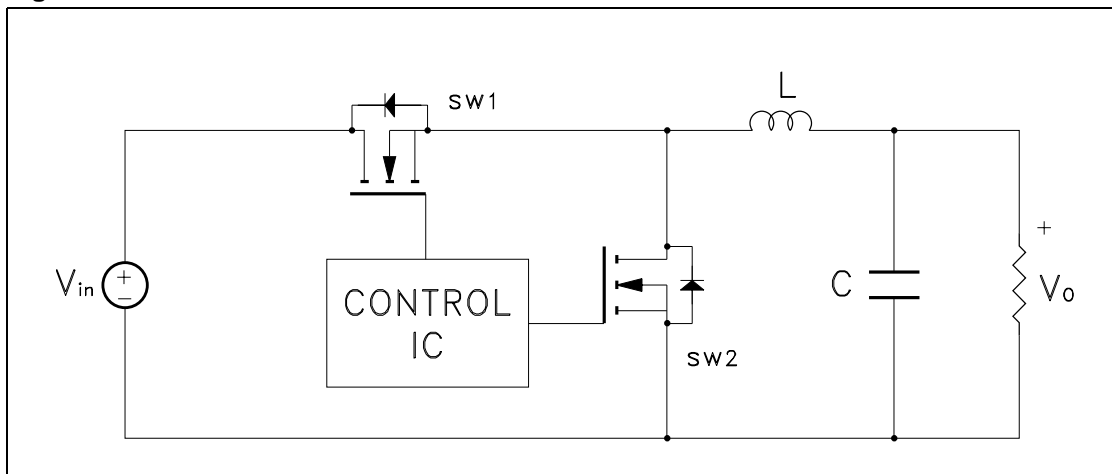
Figure 15. Unclamped Inductive load test circuit





## Appendix A

Figure 16. Buck Converter: Power Losses Estimation



The power losses associated with the FETs in a Synchronous Buck converter can be estimated using the equations shown in the table below. The formulas give a good approximation, for the sake of performance comparison, of how different pairs of devices affect the converter efficiency. However a very important parameter, the working temperature, is not considered. The real device behavior is really dependent on how the heat generated inside the devices is removed to allow for a safer working junction temperature.

The low side (SW2) device requires:

- Very low  $R_{DS(on)}$  to reduce conduction losses
- Small  $Q_{gl}$  to reduce the gate charge losses
- Small  $C_{oss}$  to reduce losses due to output capacitance
- Small  $Q_{rr}$  to reduce losses on SW1 during its turn-on
- The  $C_{gd}/C_{gs}$  ratio lower than  $V_{th}/V_{gg}$  ratio especially with low drain to source voltage to avoid the cross conduction phenomenon;

The high side (SW1) device requires:

- Small  $R_g$  and  $L_s$  to allow higher gate current peak and to limit the voltage feedback on the gate
- Small  $Q_g$  to have a faster commutation and to reduce gate charge losses
- Low  $R_{DS(on)}$  to reduce the conduction losses.

**Table 7. Power losses calculation**

		High Side Switching (SW1)	Low Side Switch (SW2)
$P_{\text{conduction}}$		$R_{\text{DS(on)SW1}} * I_L^2 * \delta$	$R_{\text{DS(on)SW2}} * I_L^2 * (1 - \delta)$
$P_{\text{switching}}$		$V_{\text{in}} * (Q_{\text{gsth(SW1)}} + Q_{\text{gd(SW1)}}) * f * \frac{I_L}{I_g}$	Zero voltage switching
$P_{\text{diode}}$	Recovery (1)	Not applicable	$V_{\text{in}} * Q_{\text{rr(SW2)}} * f$
	Conduction	Not applicable	$V_{\text{f(SW2)}} * I_L * t_{\text{deadtime}} * f$
$P_{\text{gate(QG)}}$		$Q_{\text{g(SW1)}} * V_{\text{gg}} * f$	$Q_{\text{gls(SW2)}} * V_{\text{gg}} * f$
$P_{\text{Qoss}}$		$\frac{V_{\text{in}} * Q_{\text{oss(SW1)}} * f}{2}$	$\frac{V_{\text{in}} * Q_{\text{oss(SW2)}} * f}{2}$

1. Dissipated by SW1 during turn-on

**Table 8. Paramiters meaning**

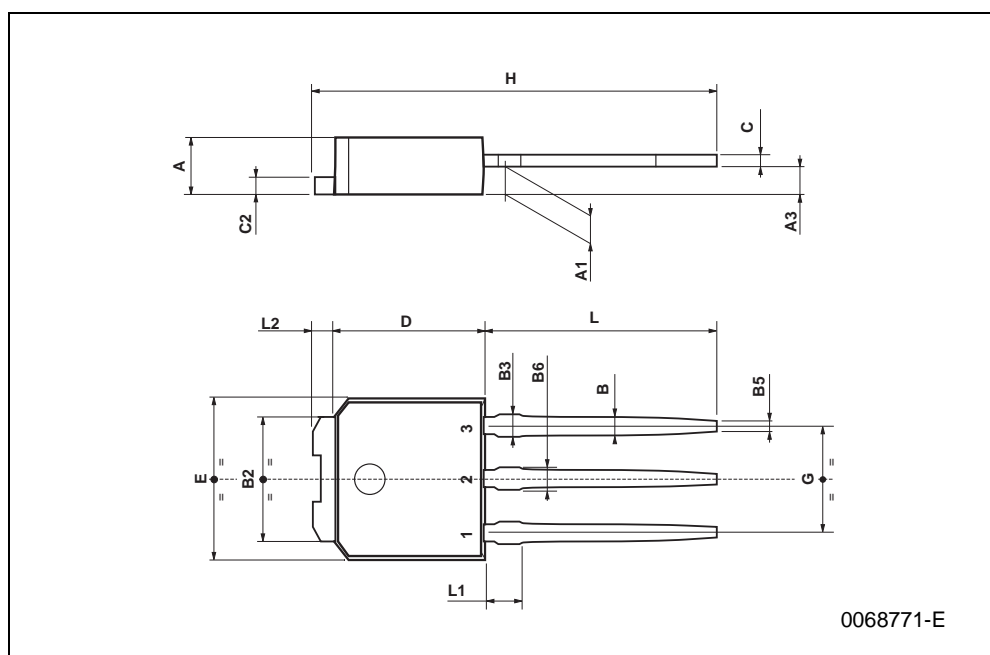
Parameter	Meaning
d	Duty-cycle
$Q_{\text{gsth}}$	Post threshold gate charge
$Q_{\text{gls}}$	Third quadrant gate charge
$P_{\text{conduction}}$	On state losses
$P_{\text{switching}}$	On-off transition losses
$P_{\text{diode}}$	Conduction and reverse recovery diode losses
$P_{\text{gate}}$	Gate drive losses
$P_{\text{Qoss}}$	Output capacitance losses

## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com)

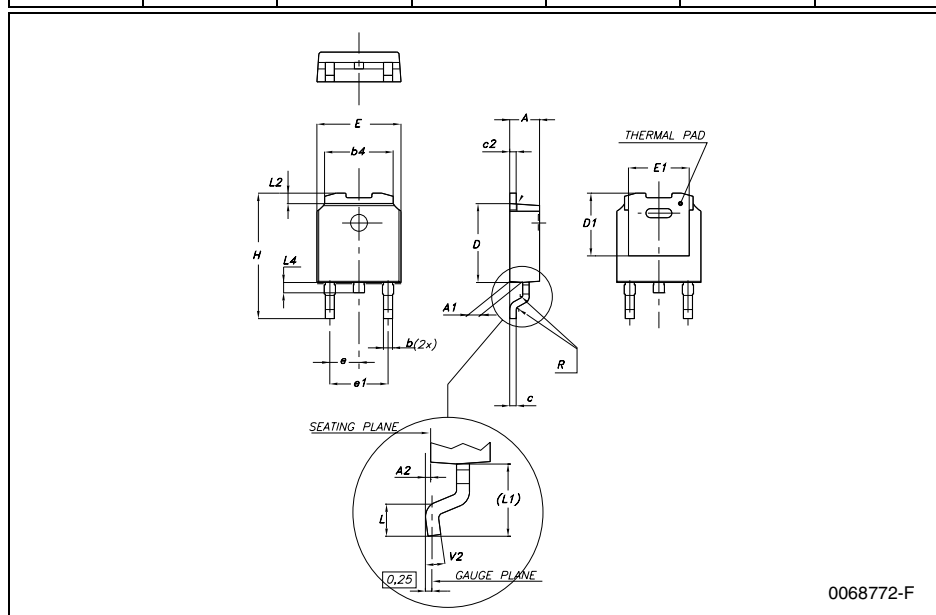
## TO-251 (IPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



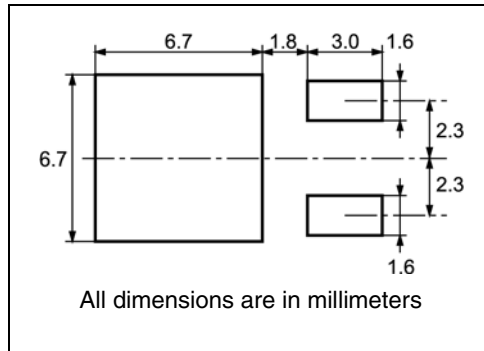
## DPAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.9	0.025		0.035
b4	5.2		5.4	0.204		0.212
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
D1		5.1			0.200	
E	6.4		6.6	0.252		0.260
E1		4.7			0.185	
e		2.28			0.090	
e1	4.4		4.6	0.173		0.181
H	9.35		10.1	0.368		0.397
L	1			0.039		
(L1)		2.8			0.110	
L2		0.8			0.031	
L4	0.6		1	0.023		0.039
R		0.2			0.008	
V2	0°		8°	0°		8°

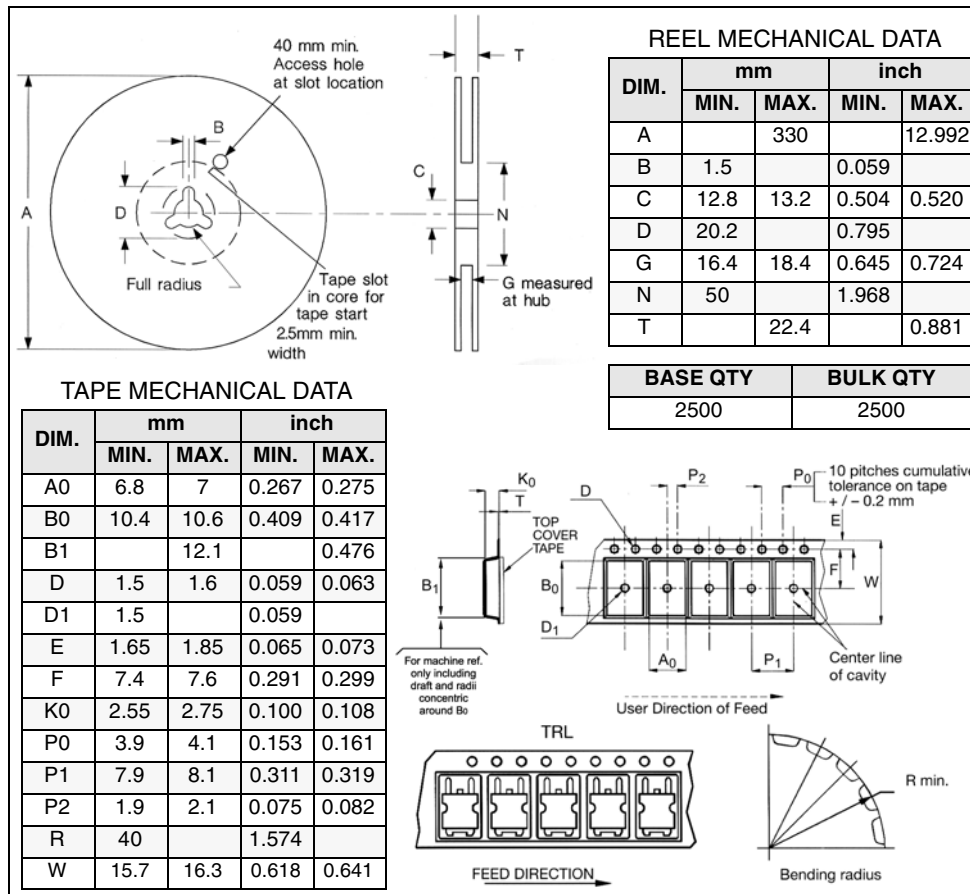


## 5 Packaging mechanical data

### DPAK FOOTPRINT



### TAPE AND REEL SHIPMENT



## 6 Revision history

**Table 9. Revision history**

Date	Revision	Changes
20-Oct-2006	1	Initial release.

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